



Title of Change:	TO247 IGBT Discrete Case Outline Standardization from 340AL to 340AM for all effected devices manufactured in On Semiconductor Vietnam and TFME facility
Proposed First Ship date:	05 Mar 2021 or earlier if approved by customer
Contact Information:	Contact your local ON Semiconductor Sales Office or Raja.Roziah.Rahmat@onsemi.com
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office or < PCN.samples@onsemi.com >. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or ffxg4t@onsemi.com
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact PCN.Support@onsemi.com
Marking of Parts/ Traceability of Change:	No Change
Change Category:	Assembly Change, Test Change
Change Sub-Category(s):	Manufacturing Site Addition

Sites Affected:**ON Semiconductor Sites****External Foundry/Subcon Sites**

ON Semiconductor Vietnam

None

Description and Purpose:

This FPCN is to inform that ON Semiconductor is migrating the TO247 IGBT discrete package case outline from 340AL to 340AM, which impacts the IGBT discrete FSII and FSIII product lines. This transition allows ON Semiconductor to standardize its portfolio on a single case outline that enable the qualifications of TO247 FSIII in ON Semiconductor Vietnam as additional assembly and final test site, apart from Tongfu Microelectronics (TFME), China.

There are no changes in product electrical specifications.

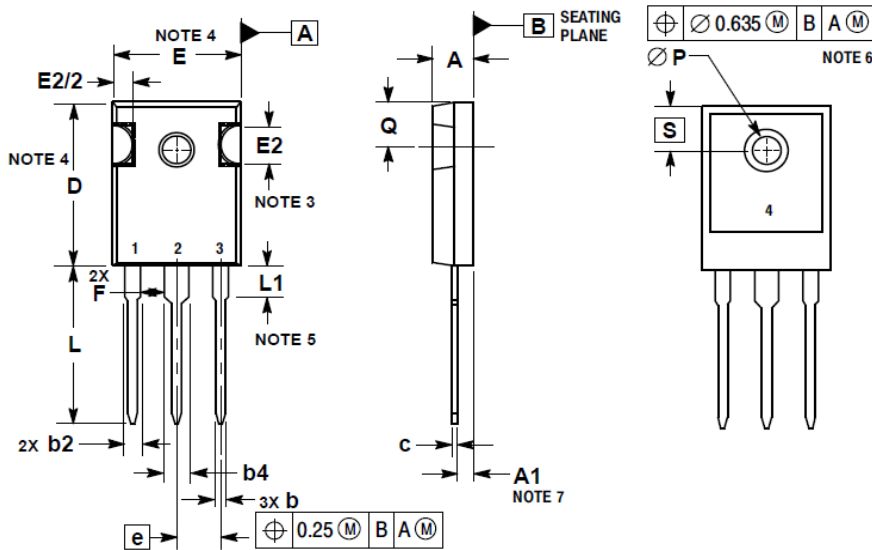
Upon the expiration of this FPCN, case outline 340AM applies for both Tongfu Microelectronics (TFME) China and On Semiconductor Vietnam (OSV).

	Before Change Description	After Change Description
Case outline	340AL	340AM
Assembly and Final Test Sites	ON Semiconductor OSV (IGBT FSII) Tongfu Microelectronics TFME (IGBT FSII, FSIII)	ON Semiconductor OSV (FSII, FSIII) Tongfu Microelectronics TFME (FSII, FSIII)

There is no product marking change as a result of this change.



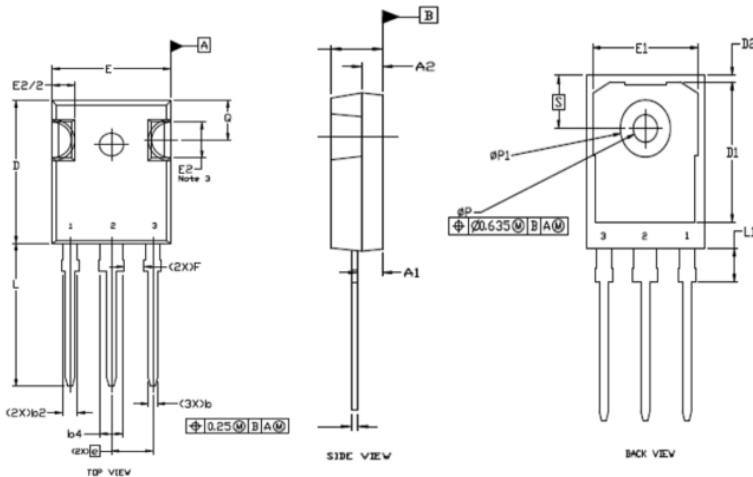
TO-247
CASE 340AL (Before Change)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
 5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
 6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
 7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

TO-247
CASE 340AM (After Change)



- NOTES:
1. DIMENSIONING AND TOLERANCE AS PER ASME Y14.5M, 2009.
 2. ALL DIMENSION ARE IN MILLIMETERS.
 3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
 4. OPTIONAL BACK SIDE HEATSINK SHAPE.
 5. DIMENSIONS ARE EXCLUSIVE OF BURRS AND MOLD FLASH. DIMENSIONS D AND E ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
 6. DIMENSIONS A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
 7. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NDM	MAX
A	4.70	5.00	5.30
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b2	1.65	2.12	2.35
b4	2.60	3.12	3.40
c	0.45	0.60	0.75
D	20.80	21.00	21.34
D1	16.30	---	---
D2	0.75	---	---
E	15.50	16.00	16.25
E1	13.80	---	---
E2	4.32	4.90	5.49
e	5.45 BSC		
F	2.655	---	---
L	19.80	20.00	20.80
L1	3.81	4.20	4.35
P	3.55	3.60	3.65
P1	6.60	---	---
Q	5.40	6.00	6.20
S	6.15 BSC		

**Reliability Data Summary:**

QV DEVICE NAME: NGTB50N120FL2WG (TIGBT - FSII)

RMS# : 70848

PACKAGE: TO247

Test	Specification	Condition	Interval	Result
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15

QV DEVICE NAME: NGTB75N65FL2WG (TIGBT – FSII)

RMS# : 70858

PACKAGE: TO247

Test	Specification	Condition	Interval	Result
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15



QV DEVICE NAME: NGTB40N135IHRWG (TIGBT – FSII)

RMS# : 70826

PACKAGE: TO247

Test	Specification	Condition	Interval	Result
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHAST	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15

QV DEVICE NAME: NGTB40N120FL3WG (TIGBT – FSIII)

RMS# : 70860

PACKAGE: TO247

Test	Specification	Condition	Interval	Result
HTRB	JESD22-A108	Ta = 145°C, bias = 80% of rated V	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/231
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/231
UHAST	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/231
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/231
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/90
SD	JSTD002	Ta = 245°C, 10 sec		0/45



QV DEVICE NAME: NGTB30N140IHR3WG (TIGBT – FSIII)

RMS# : 70862

PACKAGE: TO247

Test	Specification	Condition	Interval	Result
HTRB	JESD22-A108	Ta = 145°C, bias = 80% of rated V	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/231
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/231
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/231
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/231
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/90
SD	JSTD002	Ta = 245°C, 10 sec		0/45

Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

Part Number	Qualification Vehicle
NGTB75N65FL2WG	NGTB75N65FL2WG
NGTB60N65FL2WG	NGTB75N65FL2WG
NGTB50N65FL2WG	NGTB75N65FL2WG
NGTB50N60L2WG	NGTB75N65FL2WG
NGTB50N120FL2WG	NGTB50N120FL2WG
NGTB40N65IHL2WG	NGTB75N65FL2WG
NGTB40N65FL2WG	NGTB75N65FL2WG
NGTB40N135IHRWG	NGTB40N135IHRWG
NGTB40N120L3WG	NGTB40N120FL3WG
NGTB40N120IHRWG	NGTB40N135IHRWG



NGTB40N120FL3WG	NGTB40N120L3WG
NGTB30N120SWG	NGTB50N120FL2WG
NGTB40N120FL2WG	NGTB50N120FL2WG
NGTB35N65FL2WG	NGTB75N65FL2WG
NGTB30N140IHR3WG	NGTB30N140IHR3WG
NGTB15N135IHRWG	NGTB40N135IHRWG
NGTB30N135IHR1WG	NGTB40N135IHRWG
NGTB30N120FL2WG	NGTB50N120FL2WG
NGTB25N120FL3WG	NGTB40N120FL3WG
NGTB25N120FL2WG	NGTB50N120FL2WG
NGTB15N120IHRWG	NGTB40N135IHRWG
NGTB15N120FL2WG	NGTB50N120FL2WG
NGTG40N120FL2WG	NGTB50N120FL2WG
NGTG35N65FL2WG	NGTB75N65FL2WG
NGTG25N120FL2WG	NGTB50N120FL2WG
NGTB20N120IHRWG	NGTB40N135IHRWG
NGTB20N135IHRWG	NGTB40N135IHRWG
NGTB30N135IHRWG	NGTB40N135IHRWG
NGTB50N60SWG	NGTB75N65FL2WG
NGTB40N60L2WG	NGTB75N65FL2WG
NGTB30N65IHL2WG	NGTB75N65FL2WG
NGTB45N60SWG	NGTB75N65FL2WG

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



最終製品 / プロセス変更通知

文書番号# : FPCN23481X

発行日: 26 Nov 2020

変更件名:	オン・セミコンダクター ベトナムおよび TFME 工場で製造されるすべての影響を受ける製品について TO247 IGBT ディスクリートのケースアウトラインを 340AL から 340AM に標準化										
初回出荷予定日:	05 Mar 2021 またはお客様からの承認が得られた場合はそれ以前.										
連絡先情報:	現地のオン・セミコンダクター営業所または Raja.Roziah.Rahmat@onsemi.com にお問い合わせください。										
サンプル:	現地のオン・セミコンダクター営業所または PCN.samples@onsemi.com にお問い合わせください。サンプルは、この変更の初回通知、初回 PCN の日付から 30 日以内に要求してください。サンプル納入時は、依頼日、数量、特別梱包材/ラベル条件によって異なります。										
追加の信頼性データ:	お客様の地域のオン・セミコンダクター営業所または ffxg4t@onsemi.com にお問い合わせください。										
通知種別:	これは、お客様宛の最終製品 / プロセス変更通知 (FPCN) です。FPCN は、変更実施の 90 日前に発行されます。オン・セミコンダクターは、この通知の送付から 30 日以内に書面による問い合わせがない限り、この変更が承諾されたものとみなします。お問い合わせは、< PCN.Support@onsemi.com > 宛てにお願いします。										
変更部品の識別:	変更なし										
変更カテゴリ:	組立の変更, 検査の変更										
変更サブカテゴリ:	製造拠点の追加										
影響を受ける拠点:											
オン・セミコンダクター拠点:	外部製造工場 / 下請業者拠点:										
ON Semiconductor Vietnam	無し										
<p>説明および目的:</p> <p>本 FPCN は、オン・セミコンダクターが TO247 IGBT ディスクリートパッケージのケースアウトラインを 340AL から、IGBT ディスクリートの FSII および FSIII の製品ラインに影響を与える 340AM に移行することをお知らせするものです。この移行により、オン・セミコンダクターは単一のケースアウトラインのポートフォリオを標準化できるようになり、中国の Tongfu Microelectronics (TFME) とは別に、追加の組立および最終検査拠点としてオン・セミコンダクター ベトナムにおいて TO247 FSIII の認定が可能になります。</p> <p>製品の電氣的規格に変更はありません。</p> <p>本 FPCN 期間が満了すると、ケースアウトライン 340AM は、中国の Tongfu Microelectronics (TFME) とオン・セミコンダクター ベトナム (OSV) の両方に適用されることになります。</p> <table border="1"> <thead> <tr> <th></th> <th>変更前の表記</th> <th>変更後の表記</th> </tr> </thead> <tbody> <tr> <td>ケースアウトライン</td> <td>340AL</td> <td>340AM</td> </tr> <tr> <td>組立および最終検査拠点</td> <td>ON Semiconductor OSV (IGBT FSII) Tongfu Microelectronics TFME (IGBT FSII, FSIII)</td> <td>ON Semiconductor OSV (FSII, FSIII) Tongfu Microelectronics TFME (FSII, FSIII)</td> </tr> </tbody> </table> <p>今回の変更に伴う製品マーキングの変更はありません。</p>				変更前の表記	変更後の表記	ケースアウトライン	340AL	340AM	組立および最終検査拠点	ON Semiconductor OSV (IGBT FSII) Tongfu Microelectronics TFME (IGBT FSII, FSIII)	ON Semiconductor OSV (FSII, FSIII) Tongfu Microelectronics TFME (FSII, FSIII)
	変更前の表記	変更後の表記									
ケースアウトライン	340AL	340AM									
組立および最終検査拠点	ON Semiconductor OSV (IGBT FSII) Tongfu Microelectronics TFME (IGBT FSII, FSIII)	ON Semiconductor OSV (FSII, FSIII) Tongfu Microelectronics TFME (FSII, FSIII)									



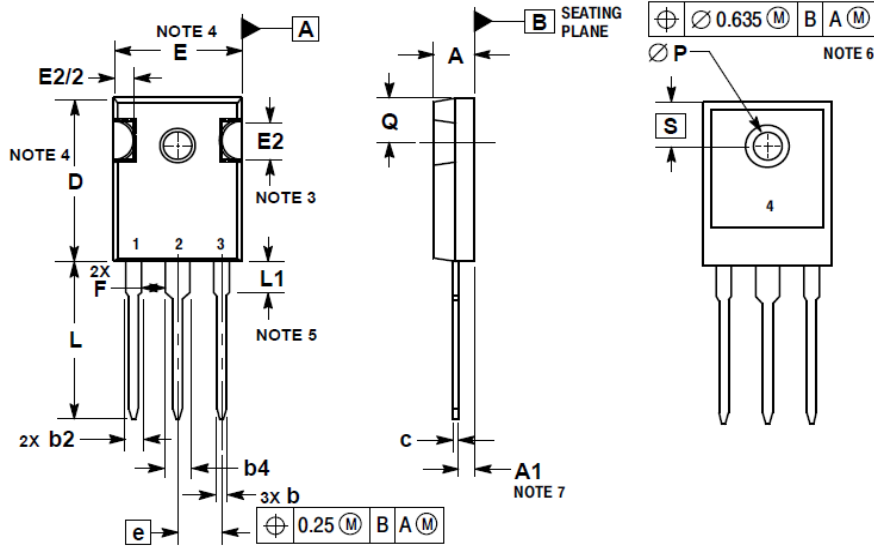
最終製品 / プロセス変更通知

文書番号# : FPCN23481X

発行日: 26 Nov 2020

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CASE 340AL (変更前の表記)



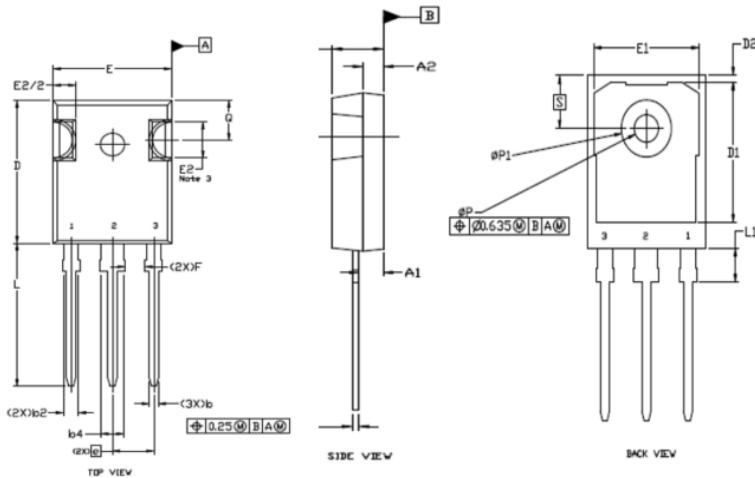
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

MILLIMETERS		
DIM	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

TO-247

CASE 340AM (変更後の表記)



NOTES:

1. DIMENSIONING AND TOLERANCE AS PER ASME Y14.5M, 2009.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. OPTIONAL BACK SIDE HEATSINK SHAPE.
5. DIMENSIONS ARE EXCLUSIVE OF BURRS AND MOLD FLASH. DIMENSIONS D AND E ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
6. DIMENSIONS A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
7. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.70	5.00	5.30
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b2	1.65	2.12	2.35
b4	2.60	3.12	3.40
c	0.45	0.60	0.75
D	20.80	21.00	21.34
D1	16.30	---	---
D2	0.75	---	---
E	15.50	16.00	16.25
E1	13.80	---	---
E2	4.32	4.90	5.49
e	5.45 BSC		
F	2.655	---	---
L	19.80	20.00	20.80
L1	3.81	4.20	4.35
P	3.55	3.60	3.65
P1	6.60	---	---
Q	5.40	6.00	6.20
S	6.15 BSC		



信頼性データの要約:

デバイス名: NGTB50N120FL2WG (TIGBT - FSII)

RMS : 70848

パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15

デバイス名: KSA1015YTA

RMS : 70858

パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15



デバイス名: NGTB40N135IHRWG (TIGBT – FSII)

RMS : 70826

パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/77
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/77
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/77
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/77
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/77
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/30
SD	JSTD002	Ta = 245°C, 10 sec		0/15

デバイス名: NGTB40N120FL3WG (TIGBT – FSIII)

RMS : 70860

パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 145°C, bias = 80% of rated V	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/231
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/231
UHASt	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/231
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/231
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/90
SD	JSTD002	Ta = 245°C, 10 sec		0/45



最終製品 / プロセス変更通知

文書番号# : FPCN23481X

発行日: 26 Nov 2020

デバイス名: NGTB30N140IHR3WG (TIGBT – FSIII)

RMS : 70862

パッケージ: TO247

テスト	仕様	条件	間隔	結果
HTRB	JESD22-A108	Ta = 145°C, bias = 80% of rated V	1008 hrs	0/231
HTGB	JESD22-A108	Ta = 175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta = 175 °C	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta = +25°C, deltaTj = 100°C max, Ton = Toff = 5min	6000 cyc	0/231
TC	JESD22-A104	Ta = -55°C to +150°C	1000 cyc	0/231
UHAST	JESD22-A102	130°C, 100% RH, 18.8psig, unbiased	96 hrs	0/231
H3TRB	JESD22-A101	85°C, 85% RH, bias = 100V max	1008 hrs	0/231
RSH	JESD22- B106	Ta = 265°C, 10 sec		0/90
SD	JSTD002	Ta = 245°C, 10 sec		0/45

電気的特性の要約:

電気的特性への影響はありません。

影響を受ける部品の一覧:

注: 部品一覧には標準部品番号 (既製品) のみが記載されています。本 PCN の影響を受けるカスタム部品番号は、PCN メールで提供される顧客個別の付録、または PCN カスタマイズポータルに記載されています。

部品番号	認定試験用ピークル
NGTB75N65FL2WG	NGTB75N65FL2WG
NGTB60N65FL2WG	NGTB75N65FL2WG
NGTB50N65FL2WG	NGTB75N65FL2WG
NGTB50N60L2WG	NGTB75N65FL2WG
NGTB50N120FL2WG	NGTB50N120FL2WG
NGTB40N65IHL2WG	NGTB75N65FL2WG
NGTB40N65FL2WG	NGTB75N65FL2WG
NGTB40N135IHRWG	NGTB40N135IHRWG
NGTB40N120L3WG	NGTB40N120FL3WG
NGTB40N120IHRWG	NGTB40N135IHRWG
NGTB40N120FL3WG	NGTB40N120L3WG



最終製品 / プロセス変更通知

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NGTB30N120SWG	NGTB50N120FL2WG
NGTB40N120FL2WG	NGTB50N120FL2WG
NGTB35N65FL2WG	NGTB75N65FL2WG
NGTB30N140IHR3WG	NGTB30N140IHR3WG
NGTB15N135IHRWG	NGTB40N135IHRWG
NGTB30N135IHR1WG	NGTB40N135IHRWG
NGTB30N120FL2WG	NGTB50N120FL2WG
NGTB25N120FL3WG	NGTB40N120FL3WG
NGTB25N120FL2WG	NGTB50N120FL2WG
NGTB15N120IHRWG	NGTB40N135IHRWG
NGTB15N120FL2WG	NGTB50N120FL2WG
NGTG40N120FL2WG	NGTB50N120FL2WG
NGTG35N65FL2WG	NGTB75N65FL2WG
NGTG25N120FL2WG	NGTB50N120FL2WG
NGTB20N120IHRWG	NGTB40N135IHRWG
NGTB20N135IHRWG	NGTB40N135IHRWG
NGTB30N135IHRWG	NGTB40N135IHRWG
NGTB50N60SWG	NGTB75N65FL2WG
NGTB40N60L2WG	NGTB75N65FL2WG
NGTB30N65IHL2WG	NGTB75N65FL2WG
NGTB45N60SWG	NGTB75N65FL2WG